

**In the Specification:**

Please amend the paragraph at page 6, line 2-12, as indicated below.

The present invention ensures accurate formation of patterns on adjacent layers of the wafer by providing accurate target location. Additionally, the present invention provides an apparatus and a method that will accurately locate a target on a wafer regardless of the flatness of the target surface. Furthermore, the present invention provides an apparatus and a method that will accurately locate the target on a wafer regardless of the asymmetry of the target surface. The proposed apparatus and method has an increased target acquisition rate, using either a conventional or a modified target. Finally, the present invention provides a target design [[is]] immune from the asymmetry and non-flat surfaces likely to arise in conventional CMP processes.

Please amend the paragraph at page 29, line 19 – page 30, line 2, as indicated below.

In summary, the present invention provides an apparatus and a method that ensures accurate formation of patterns on adjacent layers of the wafer by providing accurate target location. Additionally, the present invention provides an apparatus and a method that will accurately locate a target on a wafer regardless of the flatness of the target surface. Furthermore, the present invention provides an apparatus and a method that will accurately locate the target on a wafer regardless of the asymmetry of the target surface. The proposed apparatus and method has an increased target acquisition rate, using either a conventional or a modified target. Finally, the present invention provides a target design [[is]] immune from the asymmetry and non-flat surfaces likely to arise in conventional CMP processes.